

1. 特性

- 符合 AEC-Q100 Grade1 标准
- 集成电流检测反馈的单通道智能高边驱动
- 正常工作电压范围：4V 到 28V，AMR 40V
- 导通电阻(HD7008XXSSOP16P)：
 - 6.2 mΩ (Typ, T_J = 25°C)
 - 10.5 mΩ (Typ, T_J = 150°C)
- 输出电流：12A (typ)
- 最大限流值：80A (Typ)
- 极低待机功耗：0.1μA (Max)
- 支持深度冷启动最低供电电压 2.85V
- 兼容 3V 和 5V CMOS 输入
- CS 管脚诊断功能
 - 带高精度比例电流镜的负载电流模拟输出反馈
 - 与 V_{CC} 或结温线性相关的传感器输出
 - 输出过载和输出短路到地警报
 - OFF 状态开路负载检测
 - 输出短路到 V_{CC} 检测
 - CS 输出可启用/禁用
- 保护
 - V_{CC} 欠压关断保护
 - V_{DS} 负压钳位保护
 - 热关断警报
 - 过流保护
 - 动态过温保护
 - 通过 FaultRST 引脚可配置过热及过功率闭锁
 - 接地丢失和 V_{CC} 丢失时自动关断保护
 - 电池反接保护
 - 静电放电保护

2. 应用

- 汽车应用中后接阻性、感性和容性负载
- ADAS 系统中带保护电源：雷达和传感器
- 车灯

3. 说明

HD7008Q 是一款车规级单通道智能高边开关，其输入控制引脚兼容 3V 和 5V CMOS 接口，配有一路高功率输出通道。HD7008Q 广泛应用于汽车 12V 接地负载应用中，可以进一步提供智能保护和诊断功能。

HD7008Q 集成了先进的保护功能，包括负载过流保护、过温保护和动态过温保护等。

具有 16 个管脚的 SSOP16PP 封装版本的提供 FaultRST 引脚，其具有可配置闭锁功能的过热、过流关断保护，在出现故障时可以控制输出自动恢复或者输出闭锁。

此外，HD7008Q 内部集成专用多功能多路复用模拟输出引脚 CS，可以提供复杂的诊断功能，包括高精度比例负载电流检测，输出过载和对地短路警报，以及对 V_{CC} 短路诊断和 OFF 状态开路诊断。

HD7008MQASSOP16P 的 SEL1/SEL0 管脚还可以提供与 V_{CC} 或结温线性相关的传感器输出，以供应用系统实时监测电源电压和功率管的结温。

输入 SEn 引脚为 HD7008Q 的检测使能引脚，其可以进一步禁用 OFF 状态下的诊断功能，获得更低的功耗。此外，在同一系统使用多个 HD7008Q 的场景中，除了节省功耗外，SEn 还可以实现多片 HD7008Q 仅需一个 ADC 采样通道和一个 CS 对地电阻，从而为系统大幅降低成本。

HD7008Q 支持 SSOP16PP 和 SSOP14PP 封装，有关订购信息，请参见 Table 1。

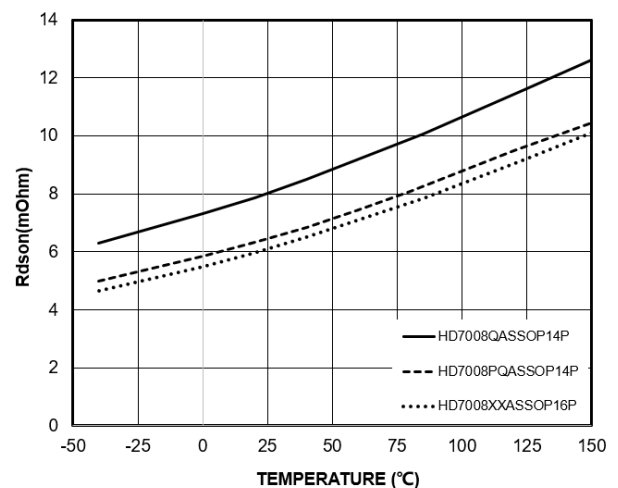


Table 1. Order Information

ORDER NUMBER	PACKAGE	MARK	VCC/Tj Sense Output	Rdson (mΩ)	ILimit (A)	TBD	RATING	PKG. Option
HD7008MQASSOP16P	SSOP16PP	HD7008MQ	Yes	6.2	80		Auto	T/R-3000
HD7008QASSOP16P	SSOP16PP	HD7008Q	No	6.2	80		Auto	T/R-3000
HD7008PQASSOP14P	SSOP14PP	HD7008PQ	No	6.5	80		Auto	T/R-3000
HD7008QASSOP14P	SSOP14PP	HD7008Q	No	8.1	80		Auto	T/R-3000

Devices can be ordered via the following two ways:

1. Place orders directly on our website (www.analogysemi.com), or;
2. Contact our sales team by mailing to sales@analogysemi.com.

4. PIN CONFIGURATION AND FUNCTIONS

Figure 1 illustrates the pin configuration of different package options.

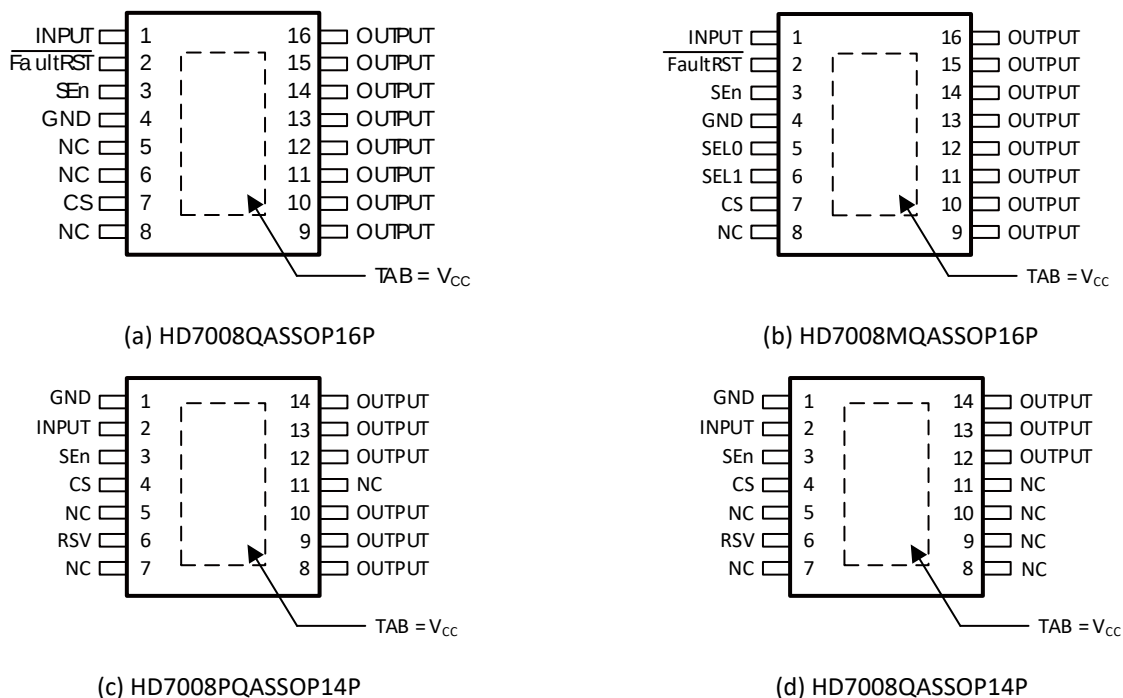


Figure 1. Pin Configuration

Table 2 lists the pin functions.

Table 2. Pin Functions

SSOP16PP Package

POSITION	NAME	TYPE	DESCRIPTION
1	INPUT	Input	Voltage controlled input pin with hysteresis, compatible with 3V and 5V CMOS outputs. It controls output switch state.
2	$\overline{\text{FaultRST}}$	Input	Active low compatible with 3V and 5V CMOS outputs pin; it unlatches the output in case of fault; If kept low, sets the outputs in auto-restart mode.
3	SEn	Input	Active high compatible with 3V and 5V CMOS outputs pin; it enables the CS diagnostic pin.
4	GND	Ground	Ground connection. Must be reverse battery protected by an external diode / resistor network.
5-6	SEL0/SEL1	Input	Active high compatible with 3 V and 5 V CMOS outputs pin; they address the CS output multiplexer. (HD7008MQASSOP16P) NC (HD7008QASSOP16P)
7	CS	Output	Analog current sense output pin. It delivers a current proportional to the load current, or fault indication, or VCC/Tj sense depending on pin5-6 configuration.
8	NC	---	Not connect for this pin.
9-16	OUTPUT	Output	Power outputs. All the pins must be connected together.
---	V _{CC}	Power	Battery connection

SSOP14PP Package

POSITION	NAME	TYPE	DESCRIPTION
1	GND	Ground	Ground connection. Must be reverse battery protected by an external diode / resistor network.
2	INPUT	Input	Voltage controlled input pin with hysteresis, compatible with 3V and 5V CMOS outputs. It controls output switch state.
3	SEn	Input	Active high compatible with 3V and 5V CMOS outputs pin; it enables the CS diagnostic pin.

4	CS	Ground	Analog current sense output pin. It delivers a current proportional to the load current, or fault indication, or VCC/Tj sense depending on pin5-6 configuration.
5	NC	Input	Not connect for this pin.
6	RSV	---	Reserved for internal use. Pulled down to GND internally. Please leave this pin floating in application.
7	NC	---	Not connect for this pin.
8-10	OUTPUT/NC	---	HD7008PQASSOP14P: Power outputs. All the pins must be connected together. HD7008QASSOP14P: Not connected for this pin.
11	NC		Not connect for this pin.
12-14	OUTPUT	Output	Power outputs. All the pins must be connected together.
---	V _{CC}	Power	Battery connection

5. SPECIFICATIONS

5.1 ABSOLUTE MAXIMUM RATINGS

Table 3 lists the absolute maximum ratings of the HD7008Q.

Table 3. Absolute Maximum Ratings

PARAMETER	DESCRIPTION	MIN	MAX	UNITS
Voltage	DC supply voltage, V_{CC}		38	V
	Reverse DC supply voltage, $-V_{CC}$		0.3	V
	Maximum transient supply voltage (ISO 16750-2:2010 Test B clamped to 40V; $R_L = 4\Omega$), V_{CCPK}		40	V
	Maximum jump start voltage for single pulse short circuit protection, V_{CCIS}		28	V
Current	DC reverse ground pin current, $-I_{GND}$		200	mA
	OUTPUT DC output current, I_{OUT}		Internally limited	A
	Reverse DC output current, $-I_{OUT}$		TBD	A
	INPUT DC input current, I_{IN}	-1	10	mA
	SEn DC input current, I_{SEn}	-1	10	mA
	SEL0/SEL1 DC input current, I_{SEL}	-1	10	mA
	FaultRST DC input current, I_{FR}	-1	1.5	mA
	CS pin DC output current ($V_{GND} = V_{CC}$ and $V_{SENSE} < 0V$), I_{SENSE}		10	mA
	CS pin DC output current in reverse ($V_{CC} < 0V$), I_{SENSE}		-20	mA
	Maximum switching energy (single pulse) ($T_{DEMAG} = 0.4ms$; $T_{JSTART} = 150^{\circ}C$), E_{MAX}		TBD	mJ
Temperature	Junction, T_J	-40	150	$^{\circ}C$
	Storage, T_{stg}	-55	150	$^{\circ}C$

Note: Stresses beyond those listed under Table 3 may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Table 5. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD RATINGS

Table 4 lists the ESD ratings of the HD7008Q.

Table 4. ESD Ratings

PARAMETER	SYMBOL	DESCRIPTION	VALUE	UNITS
Electrostatic Discharge	$V_{(ESD)}$	Human-body model (HBM), per AEC Q100-002	± 2000	V
		Human-body model (HBM), per AEC Q100-002	± 8000	
		Vcc and Output	± 8000	
		Charged-device model (CDM), per AEC Q100-011	± 1000	

5.3 RECOMMENDED OPERATING CONDITIONS

Table 5 lists the recommended operating conditions for the HD7008Q.

Table 5. Recommended Operating Conditions

PARAMETER	DESCRIPTION	SYMBOL	MIN	NOM	MAX	UNITS
POWER SUPPLY						
Power Supply			4		28	V
DIGITAL INPUTS						
Digital Input Voltage		V _{DIG}	0		5.5	V
TEMPERATURE RANGE						
Operating Ambient Temperature		T _A	−40		125	°C

5.4 THERMAL INFORMATION

Table 6 lists the thermal information for the HD7008Q.

Table 6. Thermal Information

PARAMETER	SYMBOL	Value		UNITS
		SSOP16PP	SSOP14PP	
Junction-to-Ambient Thermal Resistance	R _{θJA}	TBD	TBD	°C/W
Junction-to-Case (Top) Thermal Resistance	R _{θJC(top)}	TBD	TBD	°C/W
Junction-to-Board Thermal Resistance	R _{θJB}	TBD	TBD	°C/W
Junction-to-Top Characterization Parameter	ψ _{JT}	TBD	TBD	°C/W
Junction-to-Board Characterization Parameter	ψ _{JB}	TBD	TBD	°C/W

5.5 ELECTRICAL CHARACTERISTICS

Table 7 lists the electrical characteristics of the HD7008Q. $7V < V_{CC} < 28V$; $-40^{\circ}C < T_J < 150^{\circ}C$, unless otherwise specified. All typical values refer to $V_{CC} = 13V$; $T_J = 25^{\circ}C$, unless otherwise specified.

Table 7. Electrical Characteristics

PARAMETER		SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
DURING CRANKING							
Minimum Cranking Supply Voltage (V _{CC} Decreasing)		V _{USD_Cranking}				2.85	V
Shutdown Temperature (V _{CC} Decreasing) ⁽²⁾		T _{TSD}	V _{CC} = 2.85V; V _{CC} decreasing	140			°C
POWER							
Operating Supply Voltage		V _{CC}		4	13	28	V
Undervoltage Shutdown		V _{USD}				2.85	V
Undervoltage Shutdown Reset		V _{USDReset}				5	V
On-State Resistance ⁽¹⁾	HD7008MQASSOP16P HD7008QASSOP16P	R _{ON}	I _{OUT} = 5A; T _J = 25°C		6.2		mΩ
			I _{OUT} = 5A; T _J = 150°C			TBD	
			I _{OUT} = 5A; V _{CC} = 4V; T _J = 25°C ⁽³⁾			TBD	
	HD7008PQASSOP14P	R _{ON}	I _{OUT} = 5A; T _J = 25°C		6.5		mΩ
			I _{OUT} = 5A; T _J = 150°C			TBD	
			I _{OUT} = 5A; V _{CC} = 4V; T _J = 25°C ⁽³⁾			TBD	
	HD7008QASSOP14P	R _{ON}	I _{OUT} = 5A; T _J = 25°C		8.1		mΩ
			I _{OUT} = 5A; T _J = 150°C			TBD	
			I _{OUT} = 5A; V _{CC} = 4V; T _J = 25°C ⁽³⁾			TBD	
Supply Current in Standby at V _{CC} = 13V ⁽⁴⁾		I _{STBY}	V _{CC} = 13V; V _{IN} = V _{OUT} = V _{FR} = V _{SEn} = 0V; V _{SELO} = 0V; T _J = 25°C		0.01	0.1	μA
			V _{CC} = 13V; V _{IN} = V _{OUT} = V _{FR} = V _{SEn} = 0V; V _{SELO} = 0V; T _J = 85°C ⁽⁵⁾			TBD	
			V _{CC} = 13V; V _{IN} = V _{OUT} = V _{FR} = V _{SEn} = 0V; V _{SELO} = 0V; T _J = 125°C		0.8		
Standby Mode Blanking Time		t _{D_STBY}	V _{CC} = 13V; V _{IN} = V _{OUT} = V _{FR} = V _{SELO} = 0V; V _{SEn} = 5V to 0V		650		μs
Supply Current		I _{S(ON)}	V _{CC} = 13V; V _{SEn} = V _{FR} = V _{SELO} = 0V; V _{IN0} = 5V; V _{IN1} = 5V; I _{OUT0} = 0A; I _{OUT1} = 0A		3.3		mA
Control Stage Current Consumption in ON State. Output On.		I _{GND(ON)}	V _{CC} = 13V; V _{SEn} = 5V; V _{FR} = V _{SELO} = 0V; V _{IN0} = 5V; V _{IN1} = 5V; I _{OUT0} = 5A		3.9		mA
Off-State Output Current at V _{CC} = 13V ⁽⁴⁾		I _{L(off)}	V _{IN} = V _{OUT} = 0V; SE _n =0; V _{CC} = 13V; T _J = 25°C		0.15		μA
			V _{IN} = V _{OUT} = 0V; SE _n =0; V _{CC} = 13V; T _J = 125°C		1.2		
Output - V _{CC} Diode Voltage at T _J = 150°C		V _F	I _{OUT} = −3A; T _J = 150°C		0.7		V
SWITCHING (V _{CC} = 13V; −40°C < T _J < 150°C, UNLESS OTHERWISE SPECIFIED)							
Turn-On Delay Time at T _J = 25°C ⁽⁶⁾		t _{d(on)}	R _L = 2.6Ω		40		μs
Turn-Off Delay Time at T _J = 25°C ⁽⁶⁾		t _{d(off)}			92		
Turn-On Voltage Slope at T _J = 25°C ⁽⁶⁾		(dV _{OUT} /dt) _{on}	R _L = 2.6Ω		0.2		V/μs
Turn-Off Voltage Slope at T _J = 25°C ⁽⁶⁾		(dV _{OUT} /dt) _{off}			0.2		
Switching Energy Losses at Turn-On (t _{won})		W _{ON}	R _L = 2.6Ω	---	0.4	TBD ⁽²⁾	mJ
Switching Energy Losses at Turn-Off (t _{woff})		W _{OFF}	R _L = 2.6Ω	---	0.5	TBD ⁽²⁾	mJ
Differential Pulse Skew (t _{PHL} − t _{PLH}) ⁽⁶⁾		t _{SKEW}	R _L = 2.6Ω		62		μs

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
LOGIC INPUTS (7V < V_{CC} < 28V; -40°C < T_J < 150°C)						
INPUT Characteristics						
Input Low Level Voltage	V _{IL}				0.9	V
Low Level Input Current	I _{IL}	V _{IN} = 0.9V	0.8			μA
Input High Level Voltage	V _{IH}		2.1			V
High Level Input Current	I _{IH}	V _{IN} = 2.1V			10	μA
Input Hysteresis Voltage	V _{I(hyst)}		0.15			V
FaultRST Characteristics						
Input Low Level Voltage	V _{FRL}				0.9	V
Low Level Input Current	I _{FRL}	V _{IN} = 0.9V	0.8			μA
Input High Level Voltage	V _{FRH}		2.1			V
High Level Input Current	I _{FRH}	V _{IN} = 2.1V			10	μA
Input Hysteresis Voltage	V _{FR(hyst)}		0.15			V
SEn Characteristics						
Input Low Level Voltage	V _{FRL}				0.9	V
Low Level Input Current	I _{FRL}	V _{IN} = 0.9V	0.8			μA
Input High Level Voltage	V _{FRH}		2.1			V
High Level Input Current	I _{FRH}	V _{IN} = 2.1V			10	μA
Input Hysteresis Voltage	V _{FR(hyst)}		0.15			V
SEL1/SELO Characteristics						
Input Low Level Voltage	V _{SEnL}				0.9	V
Low Level Input Current	I _{SEnL}	V _{IN} = 0.9V	0.8			μA
Input High Level Voltage	V _{SEnH}		2.1			V
High Level Input Current	I _{SEnH}	V _{IN} = 2.1V			10	μA
Input Hysteresis Voltage	V _{SEn(hyst)}		0.15			V
PROTECTIONS (7V < V_{CC} < 18V; -40°C < T_J < 150°C)						
DC Short-Circuit Current	I _{LIMH}	V _{CC} = 13V 4V < V _{CC} < 18V ⁽²⁾		80	TBD	A
Short-Circuit Current During Thermal Cycling	I _{LIML}	V _{CC} = 13V; T _R < T _J < T _{TSD}		40		
Shutdown Temperature	T _{TSD}		155	175	200	
Reset Temperature ⁽²⁾	T _R			T _{TSD} - 10		°C
Thermal Reset of Fault Diagnostic Indication	T _{RS}	V _{FR} = 0V; V _{SEn} = 5V		135		
Thermal Hysteresis (T _{TSD} - T _R) ⁽²⁾	T _{HYST}			10		
Dynamic Temperature	ΔT _{J_SD}	V _{CC} = 13V		60		°C
Fault Reset Time for Output Unlatch ⁽²⁾	t _{LATCH_RST}	V _{FR} = 5V to 0V within 2ms after fault occurs; V _{SEn} = 5V; V _{IN} = 5V; V _{SELO} = 0V		2		
		V _{FR} = 5V to 0V longer than 2ms after fault occurs; V _{SEn} = 5V; V _{IN} = 5V; V _{SELO} = 0V		50		μs
Turn-Off Output Voltage Clamp	V _{DEMAG}	I _{OUT} = 100mA; T _J = -40°C		V _{CC} - 44		V
		I _{OUT} = 100mA; T _J = 25°C to 150°C		V _{CC} - 44		V

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
CURRENT SENSE (7V < V _{CC} < 18V; −40°C < T _J < 150°C)							
Current Sense Clamp Voltage	V _{SENSE_CL}	V _{SEn} = 0V; I _{SENSE} = 1mA		−9.3		V	
		V _{SEn} = 0V; I _{SENSE} = −1mA		5.1			
Current Sense Characteristics							
I _{OUT} /I _{SENSE}	HD7008XXSSOP16P	K ₀	I _{OUT} = 0.9A; V _{SENSE} = 0.5V; V _{SEn} = 5V		5950		
	HD7008XXSSOP14P				5450		
Current Sense Ratio Drift ⁽⁵⁾⁽⁷⁾		dK ₀ /K ₀	I _{OUT} = 0.9A; V _{SENSE} = 0.5V; V _{SEn} = 5V	TBD		TBD	%
I _{OUT} /I _{SENSE}	HD7008XXSSOP16P	K ₁	I _{OUT} = 1.5A; V _{SENSE} = 0.5V; V _{SEn} = 5V		5950		
	HD7008XXSSOP14P						
Current Sense Ratio Drift ⁽⁵⁾⁽⁷⁾		dK ₁ /K ₁	I _{OUT} = 1.5A; V _{SENSE} = 0.5V; V _{SEn} = 5V	TBD		TBD	%
I _{OUT} /I _{SENSE}	HD7008XXSSOP16P	K ₂	I _{OUT} = 6A; V _{SENSE} = 4V; V _{SEn} = 5V		5950		
	HD7008XXSSOP14P						
Current Sense Ratio Drift ⁽⁵⁾⁽⁷⁾		dK ₂ /K ₂	I _{OUT} = 6A; V _{SENSE} = 4V; V _{SEn} = 5V	TBD		TBD	%
I _{OUT} /I _{SENSE}	HD7008XXSSOP16P	K ₃	I _{OUT} = 18A; V _{SENSE} = 4V; V _{SEn} = 5V		5950		
	HD7008XXSSOP14P						
Current Sense Ratio Drift ⁽⁵⁾⁽⁷⁾		dK ₃ /K ₃	I _{OUT} = 18A; V _{SENSE} = 4V; V _{SEn} = 5V	TBD		TBD	%
CS Current for OL Detection		I _{SENSE_OL}	I _{OUT} = 0.01A; V _{SENSE} = 0.5V; V _{SEn} = 5V		2		μA
Current Sense Leakage Current		I _{SENSE0}	Current sense disabled: V _{SEn} = 0V			0.5	nA
			Current sense disabled: −1V < V _{SENSE} < 5V ⁽⁵⁾	−0.5		0.5	nA
			Current sense enabled: V _{SEn} = 5V; Channel ON; I _{OUT} = 0A; Diagnostic selected; V _{IN} = 5V; V _{SELO} = V _{SEL1} = 0V; I _{OUT0} = 0A		0.1		μA
			Current sense enabled: V _{SEn} = 5V; Channel OFF; Diagnostic selected: V _{IN0} = 0V; V _{SELO} = V _{SEL1} = 0V; I _{OUT1} = 3A		0.1		μA
CS Saturation Voltage		V _{SENSE_SAT}	V _{CC} = 7V; R _{SENSE} = 2.7kΩ; V _{SEn} = 5V; V _{IN} = 5V; V _{SELO} = 0V; I _{OUT} = 18A; T _J = −40°C		5.15		V
CS Saturation Current ⁽⁵⁾		I _{SENSE_SAT}	V _{CC} = 7V; V _{SENSE} = 4V; V _{IN} = 5V; V _{SEn} = 5V; V _{SELO} = 0V; I _{OUT} = 24A; T _a = 25°C		4.0		mA
Output Saturation Current ⁽⁵⁾		I _{OUT_SAT}	V _{CC} = 7V; V _{SENSE} = 4V; V _{IN} = 5V; V _{SEn} = 5V; V _{SELO} = 0V; T _a = 25°C	TBD			A
OFF-State Diagnostic							
OFF-State Open-Load Voltage Detection Threshold		V _{OL}	V _{SEn} = 5V; Chx OFF; Chx diagnostic selected; V _{IN0} = 0V; V _{SELO} = 0V		2.9		V
OFF-State Output Sink Current ⁽⁸⁾		I _{L(off2)}	V _{IN} = 0V; V _{OUT} = V _{OL} ; SEn = 5V; T _J = −40°C to 125°C		10		μA
OFF-State Diagnostic Delay Time from Falling Edge of Input (See Figure 6)		t _{DSTKON}	V _{SEn} = 5V; Chx ON to OFF transition; Chx diagnostic selected; e.g. Ch0: V _{IN0} = 5V to 0V; V _{SELO} = 0V; I _{OUT0} = 0A; V _{OUT} = 4V		370		μs
Settling Time for Valid OFF-State Open Load Diagnostic Indication from Rising Edge of SEn		t _{D_OL_V}	V _{IN0} = 0V; V _{IN1} = 0V; V _{FR} = 0V; V _{SELO} = 0V; V _{OUT} = 4V; V _{SEn} = 0V to 5V		55		μs
OFF-State Diagnostic Delay Time from Rising Edge of V _{OUT}		t _{D_VOL}	V _{SEn} = 5V; Chx OFF; Chx diagnostic selected; e.g. Ch0; V _{IN0} = 0V; V _{SELO} = 0V; V _{OUT} = 0V to 4V		10		μs
Chip temperature analog feedback							
MultiSense output voltage proportional to T _J ⁽¹⁰⁾		V _{SENSE_TC}	VSEn = 5 V; VSELO = 0 V; VSEL1 = 5 V; VIN = 0 V; RSENSE = 1 kΩ; Tj = -40°C		2.54		V
			VSEn = 5 V; VSELO = 0 V; VSEL1 = 5 V; VIN = 0 V; RSENSE = 1 kΩ; Tj = 25°C		2.36		V
			VSEn = 5 V; VSELO = 0 V; VSEL1 = 5 V; VIN = 0 V; RSENSE = 1 kΩ; Tj = 125°C		2.04		V
Temperature coefficient		dV _{SENSE_TC} /dT	Tj = -40°C to 150°C		−3.0		mV/°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Transfer function		$V_{SENSE_TC}(T) = V_{SENSE_TC}(T_0) + dV_{SENSE_TC} / dT * (T - T_0)$				
VCC supply voltage analog feedback						
CS output voltage proportional to VCC	VSENSE_VCC	VCC = 13 V; VSEN = 5 V; VSELO = 5 V; VSEL1 = 5 V; VIN = 0 V; RSENSE = 1 kΩ		3.3		V
Transfer function		$V_{SENSE_VCC} = V_{CC} / 4$				
Fault Diagnostic Feedback (See Table 8)						
Current Sense Output Voltage in Fault Condition	VSENSEH	VCC = 13V; RSENSE = 1kΩ e.g. Ch0 in open load: VINO = 0V; VSEN = 5V; VSELO = 0V; IOUT0 = 0A; VOUT = 4V		5.1		V
Current Sense Output Current in Fault Condition	ISENSEH	VCC = 13V; VSENSE = 5V		6.7		mA

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Current Sense Timings (Current Sense Mode - See Figure 5)⁽⁹⁾						
Current Sense Settling Time from Rising Edge of S _{En}	t _{DSENSE1H}	V _{IN} = 5V; V _{SEN} = 0V to 5V; R _{SENSE} = 1kΩ; R _L = 2.6Ω		16		μs
Current Sense Disable Delay Time from Falling Edge of S _{En}	t _{DSENSE1L}	V _{IN} = 5V; V _{SEN} = 5V to 0V; R _{SENSE} = 1kΩ; R _L = 2.6Ω		12		μs
Current Sense Settling Time from Rising Edge of INPUT	t _{DSENSE2H}	V _{IN} = 0V to 5V; V _{SEN} = 5V; R _{SENSE} = 1kΩ; R _L = 2.6Ω		110		μs
Current Sense Settling Time from Rising Edge of I _{OUT} (Dynamic Response to a Step Change of I _{OUT})	Δt _{DSENSE2H}	V _{IN} = 5V; V _{SEN} = 5V; R _{SENSE} = 1kΩ; I _{SENSE} = 90% of I _{SENSEMAX} ; R _L = 2.6Ω			30	μs
Current Sense Turn-Off Delay Time From Falling Edge of INPUT	t _{DSENSE2L}	V _{IN} = 5V to 0V; V _{SEN} = 5V; R _{SENSE} = 1kΩ; R _L = 4.3Ω		8		μs

Note 1: For each channel

Note 2: Parameter guaranteed by design and characterization; not subject to production test.

Note 3: Parameter guaranteed only at V_{CC} = 4V and T_J = 25°C

Note 4: PowerMOS leakage included

Note 5: Parameter specified by design; not subject to production test.

Note 6: See Figure 4.

Note 7: All values refer to V_{CC} = 13V; T_J = 25°C, unless otherwise specified.

Note 8: Parameter granted at -40°C < T_J < 125°C

Note 9: Transition delays are measured up to ±10% of final conditions.

Note 10: Subject to change in mass production.

TBD

Figure 2. I_{OUT}/I_{SENSE} vs. I_{OUT}

TBD

Figure 3. Current Sense Accuracy vs. I_{OUT}

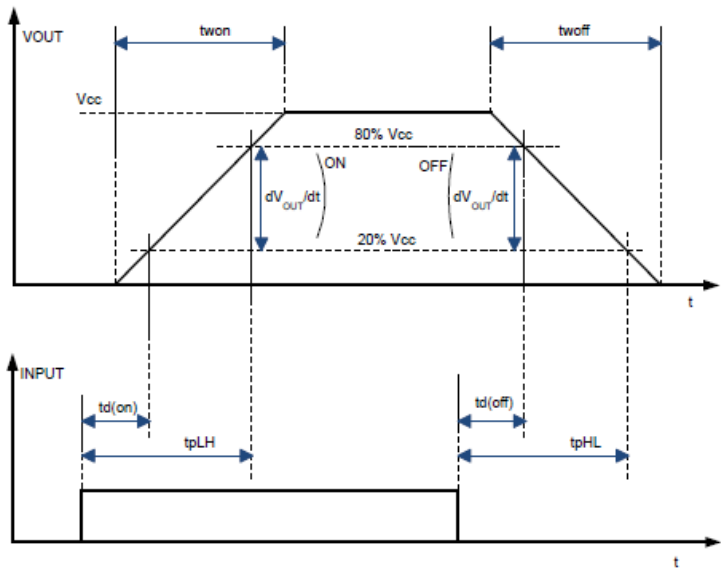


Figure 4. Switching Time and Pulse Skew

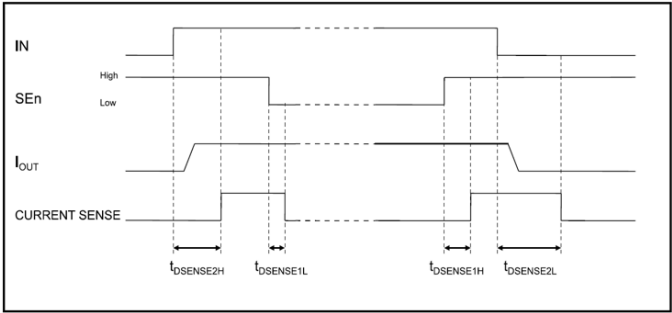


Figure 5. Current Sense Timings (Current Sense Mode)

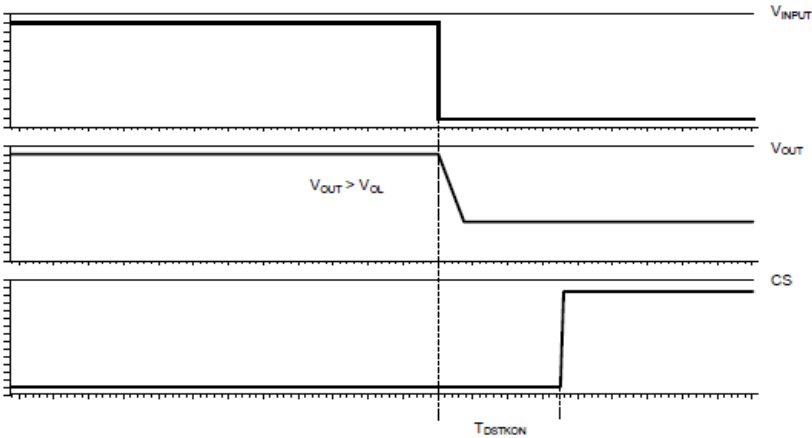


Figure 6. T_{DSTKON}

6. TYPICAL CHARACTERISTICS

TBD

Figure 7. On-State Resistance vs. T_{case}

TBD

Figure 8. On-State Resistance vs. V_{CC}

7. 详细说明

7.1 概述

HD7008Q 是一款单通道智能高边驱动，可以用于驱动各类阻性负载，感性负载和容性负载，其集成有丰富的保护和诊断功能，十分适用于各类汽车应用。在诊断功能方面，HD7008Q 集成了高精度的比例电流镜电流检测模块，可以实时检测流经负载的电流，并通过模拟 CS 引脚输出。此外，HD7008Q 还可以对过载，短路到地，短路到电源，过温以及负载开路进行诊断。所有诊断功能都可以使能或者关闭。在保护方面，HD7008Q 可以进行供电欠电压保护，过流保护，失地保护和 ESD 等保护。此外，还可以对动态过温进行保护，增加外围器件还可以实现电池反接保护。

Note

HD7008Q 提供不同的封装类型和管脚配置。下文中的系统框图和功能描述中如果出现了某个封装类型不支持的管脚定义，则可以认为所述的管脚对于此封装类型的逻辑电平为低。比如对于 HD7008QASSOP16P，其没有 SEL1/SEL0 管脚，那么下文中出现 SEL1/SEL0 功能描述的地方均应认为 SEL1 = L，SEL0 = L。

7.2 功能模块框图

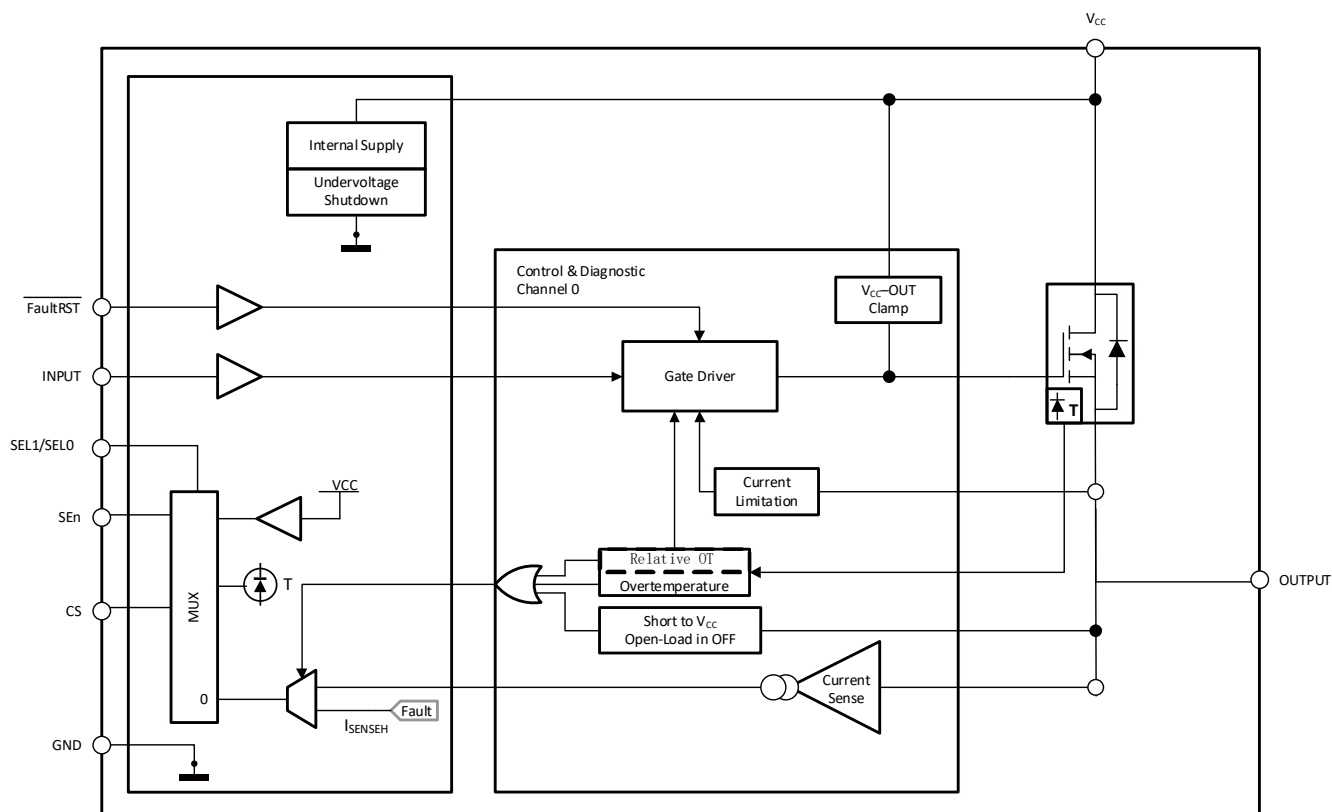


Figure 9. Functional Block Diagram

7.3 器件功能模式

7.3.1 进入和离开 STANDBY 工作模式

如下图所示，进入和退出 Stand-by 模式可以通过控制输入引脚高低实现。这里请注意，退出 stand-by 模式只能通过 INPUT 或者 SEn 拉高实现。

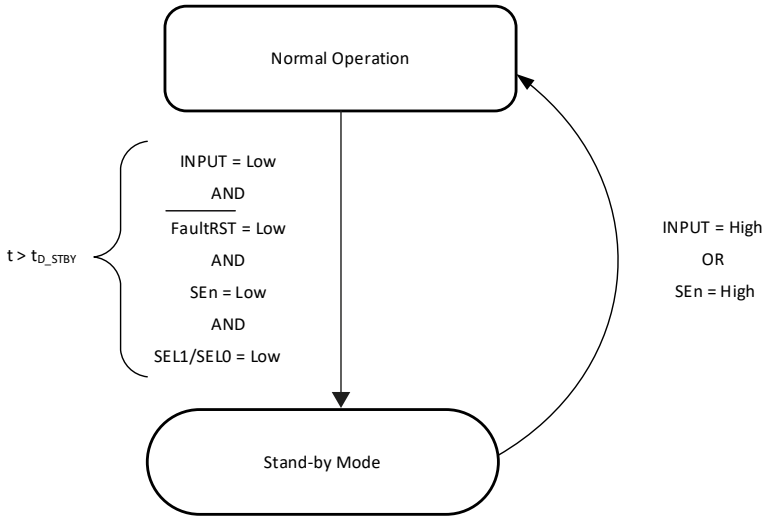


Figure 10. Standby State Diagram

一旦芯片从 Normal operation mode 进入 standby mode 后，应保证 20us 内不再次进入 normal operation mode，以使得芯片内部电路有足够的下电及重新建立时间，否则可能会引起在芯片在完全进入 standby mode 前开关功能不正常。如果应用中某通道要求从关闭后到重新开启的时间落在 td_stby 范围内 (比如 PWM 控制等场景)，那么可以通过把 SEn 或 FaultRst 或 SELx 管脚置高的方式强制芯片不进入 standby mode。

7.3.2 工作模式配置真值表

除了正常工作模式和 stand-by 外，HD7008Q 还有可能出现例如过载、欠压、诊断和负压钳位的状态。下表列出各种状态模式下条件和各个管脚的状态：

Table 8. Truth Table

MODE	CONDITIONS	IN	FR	SEn	-	OUT	CURRENT SENSE	COMMENTS
Standby	All logic inputs low	L	L	L	-	L	Hi-Z	Low quiescent current consumption
Normal	Nominal load connected; $T_J < 150^{\circ}\text{C}$	L	L	See Table 9		L	See Table 9	
		L	H			L		
		H	L			H		Outputs configured for auto-restart
		H	H			H		Outputs configured for latch-off
Overload	Overload or short to GND causing: $T_J > T_{TSD}$ or $\Delta T_J > \Delta T_{J_SD}$	L	X			L		
		H	L			H		Output cycles with temperature hysteresis
		H	H			L		Output latches-off
Undervoltage	$V_{CC} < V_{USD}$ (falling)	X	X	X	-	L	Hi-Z	Re-start when $V_{CC} > V_{USD} + V_{USDhyst}$ (rising)
OFF-State Diagnostics	Short to V_{CC}	L	X	See Table 9		H	See Table 9	
	Open-load	L	X			H		External pull-up
Negative Output Voltage	Inductive loads turn-off	L	X			< 0V		

电流，结温，VCC 电压检测多路复用寻址真值表

Table 9. Current Sense Multiplexer Addressing

SEn	SEL1	SEL0	MUX CHANNEL	CURRENT SENSE OUTPUT			
				NORMAL MODE	OVERLOAD	OFF-STATE DIAG. ⁽¹⁾	NEGATIVE OUTPUT
L	X	X		Hi-Z			
H	L	L	Output diagnostic	I _{SENSE} = 1/K * I _{OUT}	V _{SENSE} = V _{SENSEH}	V _{SENSE} = V _{SENSEH}	Hi-Z
H	L	H					
H	H	L	Tj Sense	V _{SENSE} = V _{SENSE_TC}			
H	H	H	VCC Sense	V _{SENSE} = V _{SENSE_VCC}			

7.3.3 LATCH 功能描述

TBD

Figure 11. Latch Functionality - Behavior in Hard Short-Circuit Condition ($T_{AMB} << T_{TSD}$)

TBD

Figure 12. Latch Functionality - Behavior in Hard Short-Circuit Condition

TBD

Figure 13. Latch Functionality - Behavior in Hard Short-Circuit Condition (Autorestart Mode + Latch Off)

7.4 特性描述

7.4.1 保护

7.4.1.1 欠压保护

HD7008Q 具备欠压保护功能，当芯片供电电压 V_{CC} 降低至 V_{USD} 以下时，会触发芯片复位功能，此时无论输入状态如何，输出都将处于关闭状态。 V_{USD} 最大值为 2.85V，该功能使得 HD7008Q 支持深度冷启动最低供电电压 2.85V 要求。

7.4.1.2 动态过温保护 (DYNAMIC OVER TEMPERATURE SHUTDOWN)

动态过温保护的基本工作原理是通过测量芯片内部的空间温度梯度来间接测量结温摆幅 ΔT_J ，以便在 ΔT_J 超过 ΔT_{J_SD} 的安全水平时自动关断输出 MOSFET。该保护可防止快速热瞬态效应，从而减少热机械疲劳。功率管关闭后，芯片结温会下降， ΔT_J 也会减小，当 ΔT_J 重新回到 $\Delta T_{J_SD} - 10^\circ\text{C}$ 以下时，芯片会根据 FaultRST 引脚上的电平，尝试重新启动 (FaultRST = 低) 或保持关闭状态 (FaultRST = 高)。

动态过温保护发生时，如果 SEN 为高电平，CS 引脚会输出 I_{SENSEH} 进行故障报警，CS 管脚的电压由外部的下拉电阻决定，但最大输出电压限制在 V_{SENSE_CL} 以下。

7.4.1.3 过温关断保护 (THERMAL SHUTDOWN)

如果 HD7008Q 的结温超过最大允许阈值 (典型值为 175°C)，它会自动关闭发生过温的通道。当结温降至 T_R 以下后，芯片会根据 FaultRST 引脚上的电压电平，尝试重新启动 (FaultRST = 低) 或保持关闭状态 (FaultRST = 高)。

当芯片检测到过温事件后，如果 SEN 为高电平，CS 引脚会输出 I_{SENSEH} 进行故障报警，CS 管脚的电压由外部的下拉电阻决定，但最大输出电压限制在 V_{SENSE_CL} 以下。

7.4.1.4 过流保护 (OVER CURRENT LIMITATION)

HD7008Q 内部集成了一个输出电流过流保护模块，从而有效的保护芯片自身以及系统中的其他组件 (例如键合线、线束、连接器、负载等)，使其免受大电流的影响而损害。在发生短路、过载或过载上电期间，过流保护门限为 I_{LMH} 。如果芯片处于自动恢复模式，那么过流保护被触发后，第二次过流保护门限会自动变成 $0.5 \times I_{LIML}$ 。

7.4.1.5 负压钳位保护 (NEGATIVE VOLTAGE CLAMP)

如果器件驱动感性负载，则输出电压在关断期间达到负值。负电压钳位结构将最大负电压限制在特定值 V_{DEMG} ，从而允许在不损坏器件的情况下耗散电感器能量。

7.4.1.6 接地丢失 (LOSS OF GROUND) AND 供电丢失 (LOSS OF VCC)

如果芯片发生了接地丢失，芯片地会浮空并且电位大概为供电电压，芯片此时会自动关闭两个通道的输出，从而使得负载和地之间不会有电流流出。输入控制引脚由于有输入电阻的保护，也不会有安全问题。

如果芯片发生供电丢失问题，那么芯片会有欠压保护功能，保证芯片可以自动关闭输出，实现保护。

7.4.1.7 电池反接保护

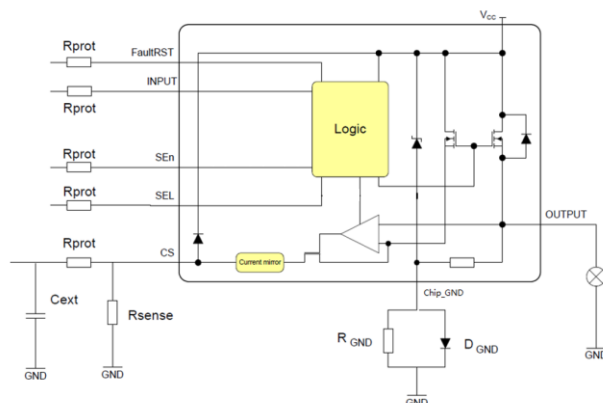


Figure 14. Simplified Internal Structure

对于需要支持电池反接的应用，建议在芯片地和 PCB 地之间增加如上图所示的电池反接保护网络，即上图 R_{GND}(typ. R_{GND} = 4.7kΩ)并联一个二极管。这样可以限制电池反接场景时通过芯片的电流，避免芯片损坏。

7.4.1.8 MCU IO 保护

在使用接地保护网络时，如果 V_{cc} 存在负压瞬变，则输入控制引脚将被拉至负压。针对这种场景，建议插入一个保护电阻 (R_{prot})，这样既可以防止微控制器的 I/O 引脚门锁，也能有效保护 HD7008Q 的输入引脚。

这些保护电阻的阻值推荐为：R_{prot} = 15kΩ.

7.4.2 诊断

7.4.2.1 高精度电流检测

芯片和负载状态的诊断信息由模拟输出引脚(CS)提供通道输出电流的正比例输出和故障指示。HD7008MQSSOP16P 还提供与 VCC 和结温线性相关的电流输出。这些信号通过模拟多路复用器进行输出，该多路复用器通过 SEL0/1 和 SEn 配置和控制。

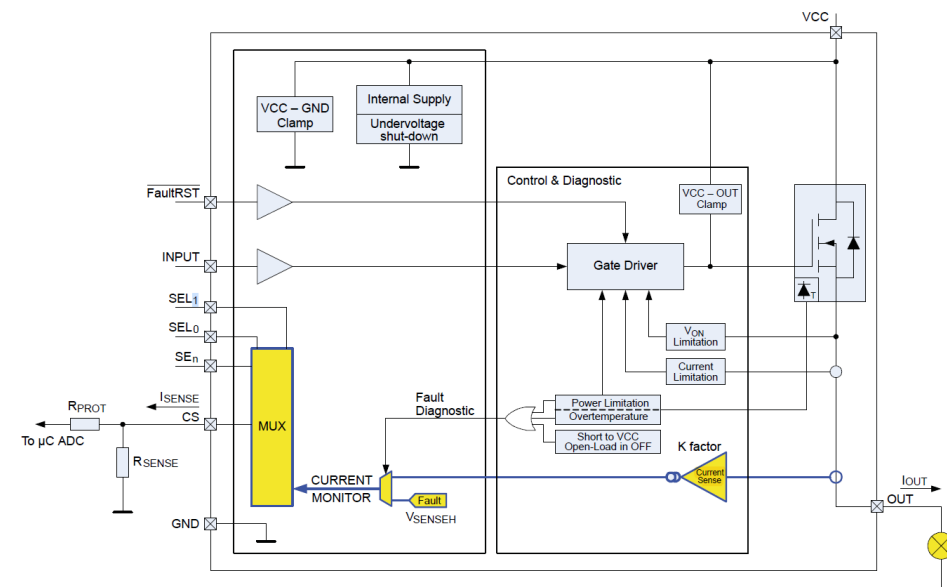


Figure 15. 电流监测

CS 引脚可以提供如下信息：

1. 与负载电流成正比的电流，该比例为已知比例 k ；
2. 在故障条件下提供诊断标志，其电压为固定电压 V_{SENSEH} ；
3. 与 VCC 线性相关的电流输出，如果 CS 管脚上由 $1k\Omega$ 的对地电阻，则传输函数为 $V_{SENSE_VCC} = V_{CC} / 4$ ；
4. 与结温线性相关的电流输出，如果 CS 管脚上由 $1k\Omega$ 的对地电阻，则传输函数为 $V_{SENSE_TC}(T) = V_{SENSE_TC}(T_0) + dV_{SENSE_TC} / dT * (T - T_0)$ ；

电流检测电路 I_{SENSE} 提供的电流可以通过使用外部检测电阻 R_{SENSE} 转换为电压 V_{SENSE} ，从而实现连续负载监控和异常情况检测。

在 Normal 工作模式下(没有故障)， V_{SENSE} 的计算公式如下：

$$\text{CS 的电流 } I_{SENSE} = I_{OUT} / K$$

$$\text{CS 的电压: } V_{SENSE} = R_{SENSE} \times I_{SENSE} = R_{SENSE} \times I_{OUT} / K$$

其中：

- V_{SENSE} 的电压可以通过对外部 R_{SENSE} 进行测量。
- I_{SENSE} 是 CS 输出的电流。
- I_{OUT} 是输出负载电流。
- K 是固定的输出电流和内部监测电流模块的比例。

7.4.2.2 过载和短路到地

过载主要指动态过温保护或者过温关断保护，而输出短路到地则会触发过流保护或者过温保护，以上两种情况都会通过 CS 输出报警。

7.4.2.3 离线负载开路诊断和短路到 VCC 诊断

在进行离线负载诊断时，其示意图如下图所示：

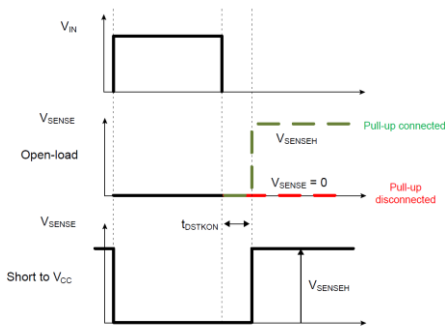


Figure 16. Open-Load / Short to VCC Condition

下表表明了开路，短路到 VCC 以及正常条件下的输出、CS 和 SEn 的情况：

Table 10. Current Sense Pin Levels in Off-State

CONDITION	OUTPUT	CS	SEn
Open-Load	$V_{OUT} > V_{OL}$	Hi-Z	L
		V_{SENSEH}	H
	$V_{OUT} < V_{OL}$	Hi-Z	L
		0	H
Short to VCC	$V_{OUT} > V_{OL}$	Hi-Z	L
		V_{SENSEH}	H
Nominal	$V_{OUT} < V_{OL}$	Hi-Z	L
		0	H

7.4.2.3.1 离线负载诊断

在关闭模式下检测开路负载需要一个外部上拉电阻 RPU 将输出连接到正电源电压 VPU。最好在模块待机模式期间关闭 VPU，以避免在正常情况下(即连接负载时)整体待机电流消耗增加。必须根据以下等式选择 RPU 以确保 $V_{OUT} > V_{OLmax}$ ：

$$R_{PU} < \frac{V_{PU} - 4}{I_{L(off2)min@4V}}$$

7.4.2.3.2 短路到 VCC 诊断

VCC 和输出之间的短路由在器件关闭状态期间设置为 VSENSEH 的相关电流检测引脚指示。根据短路的具体情况，在导通状态期间电流感测器传送小电流或不传送电流。

7.5 VCC=16V 下最大退磁能量

HD7008Q 输出接感性负载时，其供电电压 V_{CC} 为 16V，负载等效电感 L 会限制其允许工作的最大连续电流。详细请参考下图：

TBD

请注意，输出为感性负载的应用可以通过上图获得负载等效电感条件下的最大允许电流，然后根据电流和此时的 V_{CC} 值，在 PWM 控制模式下计算输出最大占空比。所有控制建议在最大允许值范围内，以保证芯片正常工作不会损坏。此外，上图数据只是典型值，仅供参考，实际真正的边界值，请联系类比技术支持获得更加详细的数据。

8. 应用与实现

注

以下应用部分中的信息不是公司组件规范的一部分，公司不保证其准确性或完整性。公司的客户有责任确定组件是否适合他们的用途。客户应验证和测试他们的设计实施以确认系统功能。

8.1 应用参考框图

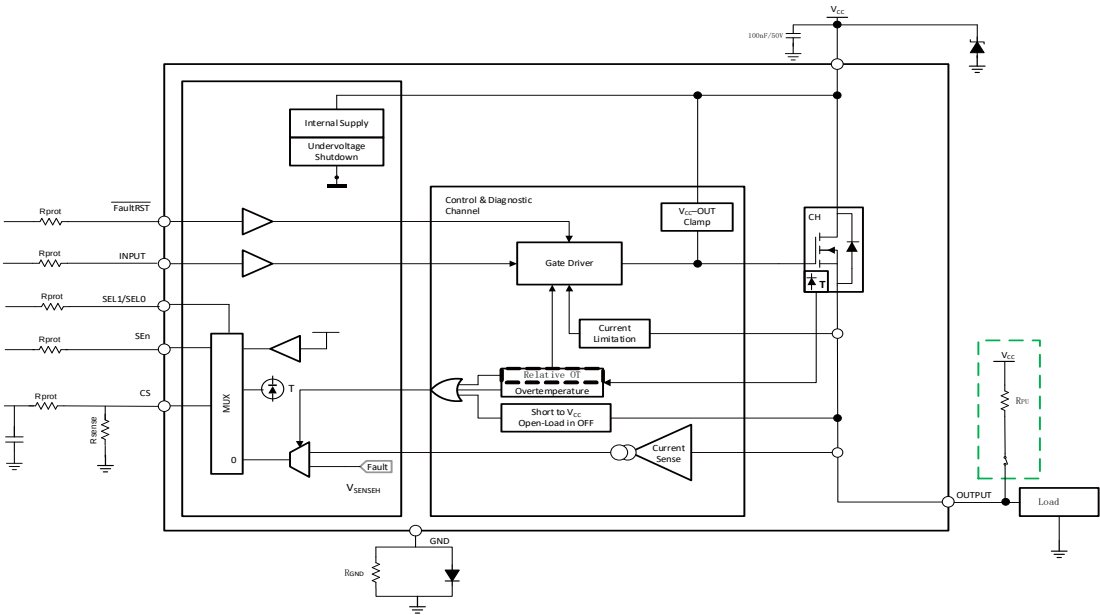


Figure 17. Application Diagram

8.2 未使用引脚或者 NC 引脚接法推荐

CONNECTION / PIN	CS	NC	OUTPUT	INPUT	SEn, FaultRST
Floating	Not allowed	X	X	X	X
To ground	Through 1kΩ resistor	X	Not allowed	Through 15kΩ resistor	Through 15 kΩ resistor

Note: X: Do NOT care.

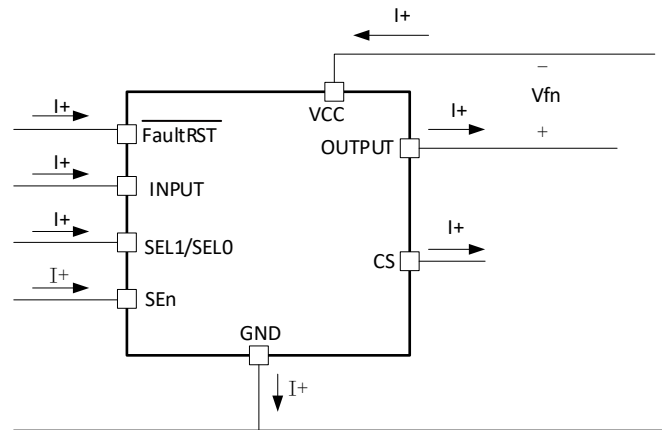


Figure 18. Current and Voltage Conventions

Note:

1. $V_{Fn} = V_{OUT} - V_{CC}$ during reverse battery condition.
2. All other pin voltages are referred to GND

8.3 IMMUNITY AGAINST TRANSIENT ELECTRICAL DISTURBANCES

9. LAYOUT

9.1 LAYOUT GUIDELINES

10. PACKAGE INFORMATION

The HD7008Q is available in the SSOP16PP and SSOP14PP package. [Figure 19](#) and [Figure 20](#) show the package view.

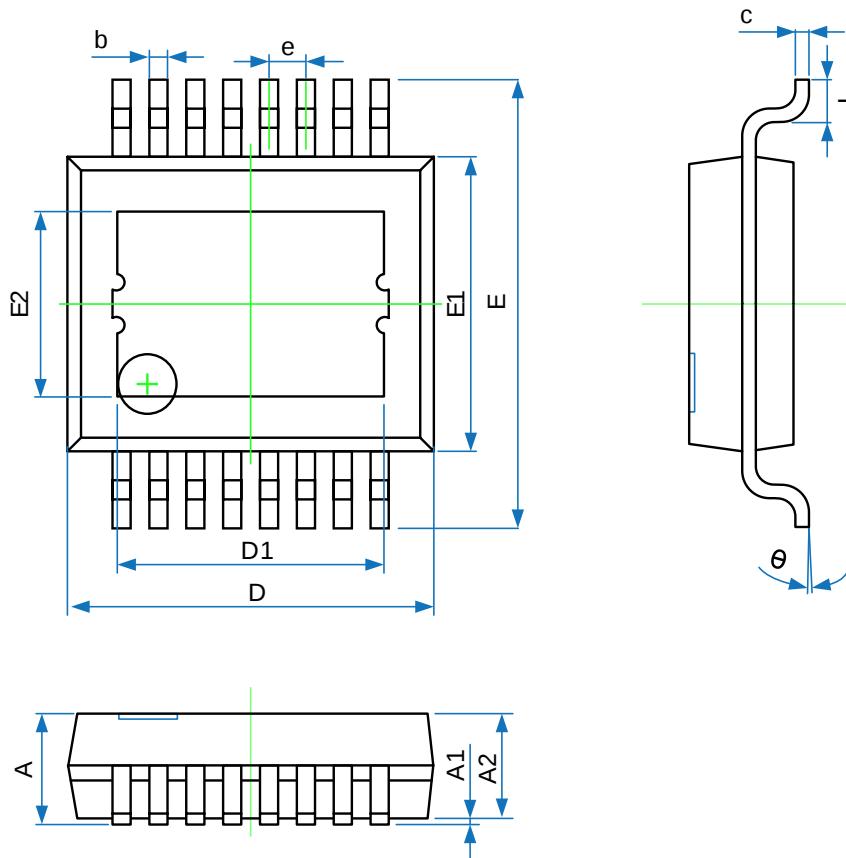


Figure 19. Package View of SSOP16PP

[Table 11](#) provides detailed information about the dimensions.

Table 11. Dimensions

SYMBOL	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES	
	MIN	MAX	MIN	MAX
A	1.350	1.650	0.053	0.065
A1	0.000	0.100	0.000	0.004
A2	1.350	1.550	0.053	0.061
b	0.200	0.300	0.008	0.012
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
D1	3.510	3.710	0.138	0.146
E	6.050	6.200	0.238	0.244
E1	3.800	4.000	0.150	0.157
E2	2.400	2.600	0.094	0.102
e	0.500 (BSC)		0.020 (BSC)	
L	0.400	0.900	0.016	0.035
θ	0°	8°	0°	8°

Figure 20 shows the SSOP14PP package view.

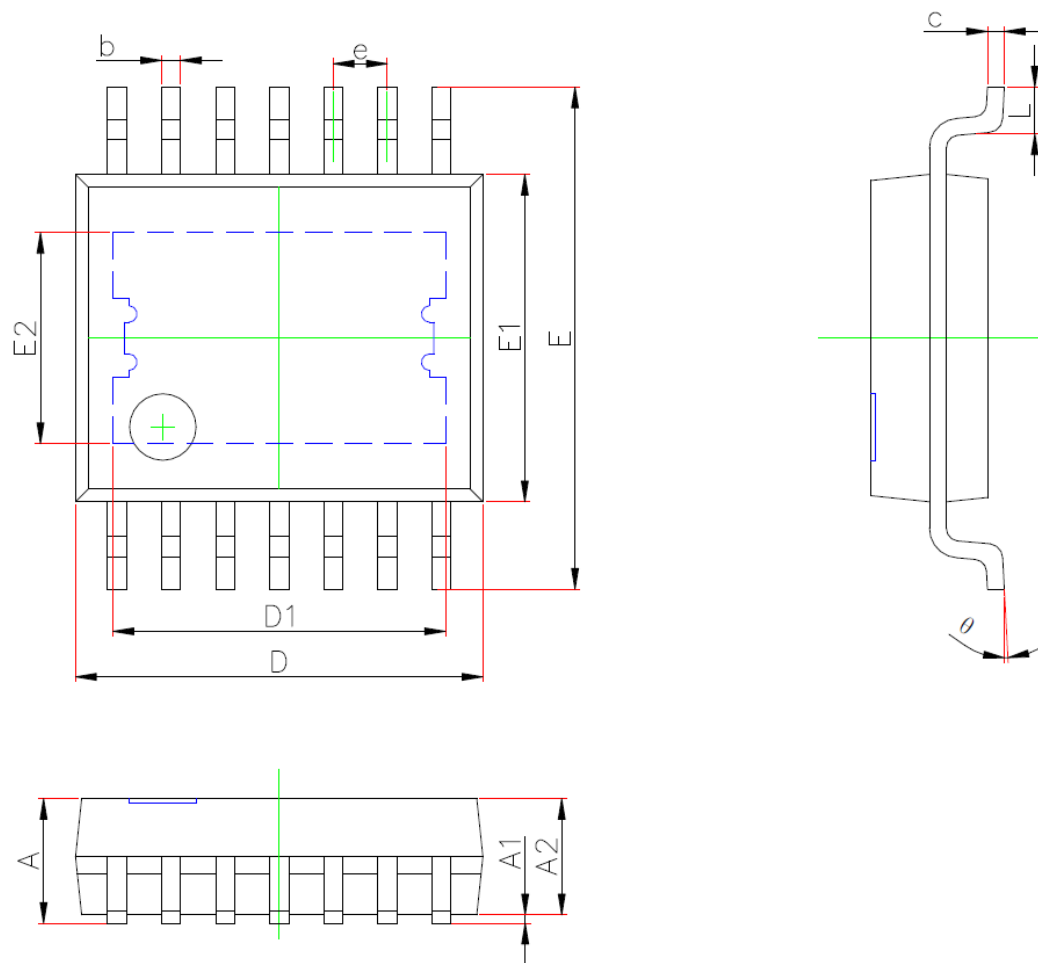


Figure 20. Package View of SSOP14PP

Table 12 provides detailed information about the dimensions.

Table 12. Dimensions

SYMBOL	DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES	
	MIN	MAX	MIN	MAX
A	1.350	1.650	0.053	0.065
A1	0.000	0.100	0.000	0.004
A2	1.350	1.550	0.053	0.061
b	0.200	0.300	0.008	0.012
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
D1	3.900	4.100	0.154	0.161
E	6.050	6.200	0.238	0.244
E1	3.800	4.000	0.150	0.157
E2	2.440	2.640	0.096	0.104
e	0.6500 (BSC)		0.026 (BSC)	
L	0.400	0.900	0.016	0.035
θ	0°	8°	0°	8°

11. TAPE AND REEL INFORMATION

TBD